

# MOSFET – Power, Single, N-Channel with ESD Protection, SOT-723 20 V, 890 mA

## NTK3134N

### Features

- N-Channel Switch with Low  $R_{DS(on)}$
- 44% Smaller Footprint and 38% Thinner than SC89
- Low Threshold Levels Allowing 1.5 V  $R_{DS(on)}$  Rating
- Operated at Low Logic Level Gate Drive
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Load/Power Switching
- Interface Switching
- Logic Level Shift
- Battery Management for Ultra Small Portable Electronics

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

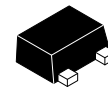
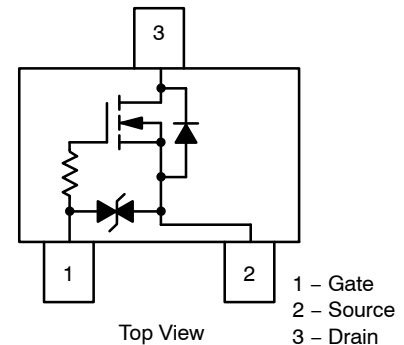
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DS}$	20	V
Gate-to-Source Voltage			$V_{GS}$	$\pm 8$	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	890	mA
		$T_A = 85^\circ\text{C}$		640	
	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$		990	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	450	mW
	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$		550	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	750	mA
		$T_A = 85^\circ\text{C}$		540	
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	$P_D$	310	mW
Pulsed Drain Current	$t_p = 10 \mu\text{s}$		$I_{DM}$	1.8	A
Operating Junction and Storage Temperature			$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
2. Surface mounted on FR4 board using the minimum recommended pad size

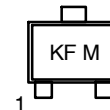
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ Max
20 V	0.20 $\Omega$ @ 4.5 V	890 mA
	0.26 $\Omega$ @ 2.5 V	790 mA
	0.43 $\Omega$ @ 1.8 V	700 mA
	0.56 $\Omega$ @ 1.5 V	200 mA

### SOT-723 (3-LEAD)



SOT-723  
CASE 631AA  
STYLE 5

### MARKING DIAGRAM



KF = Specific Device Code  
M = Date Code

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTK3134NT1G	SOT-723 Pb-Free	4000 / Tape & Reel
NTK3134NT1H		4000 / Tape & Reel
NTK3134NT5G		8000 / Tape & Reel
NTK3134NT3G		40000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	280	°C/W
Junction-to-Ambient – $t = 5$ s (Note 3)	$R_{\theta JA}$	228	
Junction-to-Ambient – Steady State Minimum Pad (Note 4)	$R_{\theta JA}$	400	

3. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)  
4. Surface mounted on FR4 board using the minimum recommended pad size

# MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\text{ }\mu\text{A}$ , Reference to $25^\circ\text{C}$		18		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		2.0	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			$\pm 0.5$	$\mu\text{A}$

## ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	0.45		1.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 890\text{ mA}$		0.20	0.35	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 780\text{ mA}$		0.26	0.45	
		$V_{GS} = 1.8\text{ V}, I_D = 700\text{ mA}$		0.43	0.65	
		$V_{GS} = 1.5\text{ V}, I_D = 200\text{ mA}$		0.56	1.2	
Forward Transconductance	$g_{FS}$	$V_{DS} = 10\text{ V}, I_D = 800\text{ mA}$		1.6		S

## CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 16\text{ V}$		79	120	pF
Output Capacitance	$C_{OSS}$			13	20	
Reverse Transfer Capacitance	$C_{RSS}$			9.0	15	

## SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)

Turn On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}, I_D = 500\text{ mA}, R_G = 10\text{ }\Omega$		6.7		ns
Rise Time	$t_r$			4.8		
TurnOff Delay Time	$t_{d(OFF)}$			17.3		
Fall Time	$t_f$			7.4		

## DRAIN SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 350 mA	T <sub>J</sub> = 25°C		0.75	1.2	V	
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>SD</sub> /d <sub>t</sub> = 100 A/μs, I <sub>S</sub> = 1.0 A, V <sub>DD</sub> = 20 V				8.1	ns	
Charge Time	t <sub>a</sub>					6.4		
Discharge Time	t <sub>b</sub>					1.7		
Reverse Recovery Charge	Q <sub>RR</sub>					3.0		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width = 300  $\mu\text{s}$ , duty cycle = 2%  
6. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

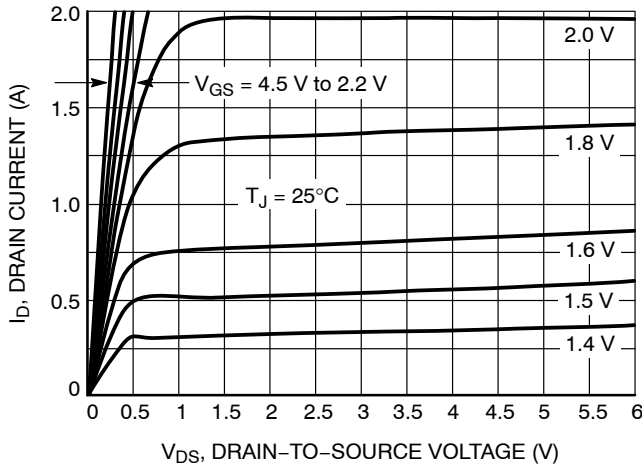


Figure 1. On-Region Characteristics

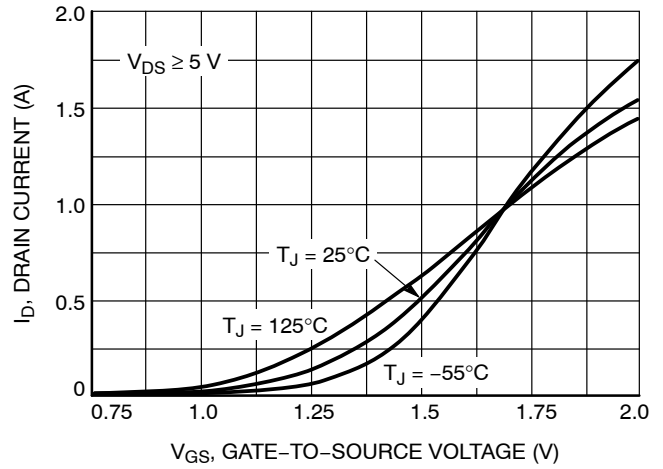


Figure 2. Transfer Characteristics

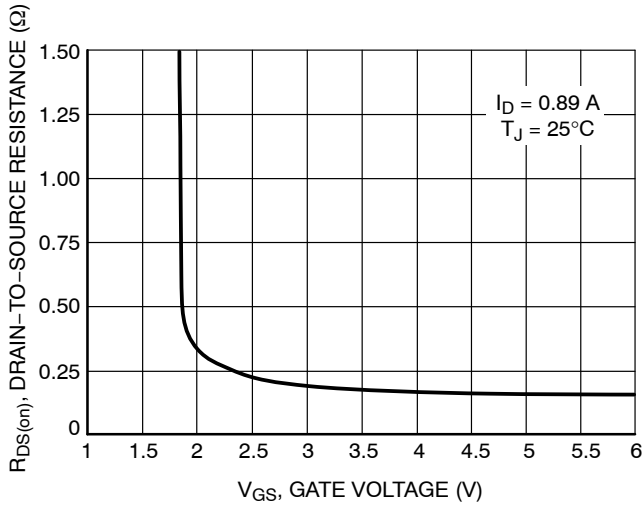


Figure 3. On-Resistance vs. Gate-to-Source Voltage

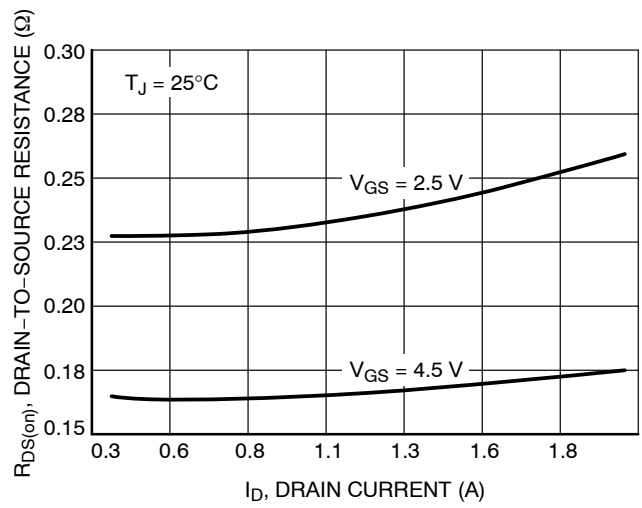


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

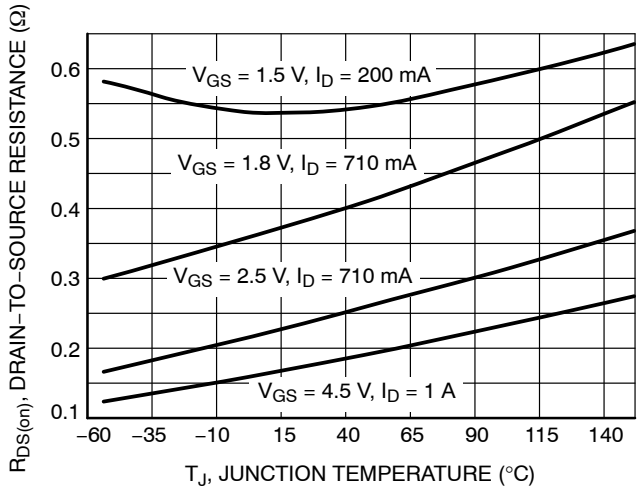


Figure 5. On-Resistance Variation with Temperature

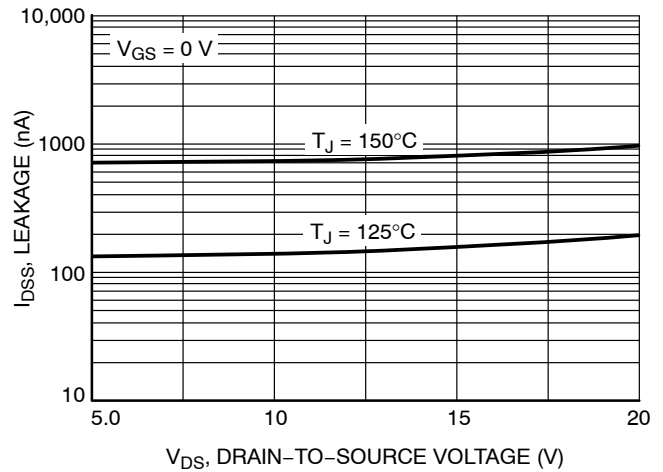


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

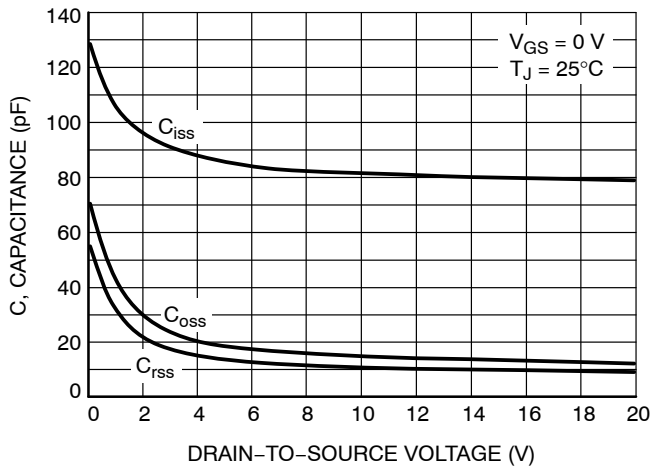


Figure 7. Capacitance Variation

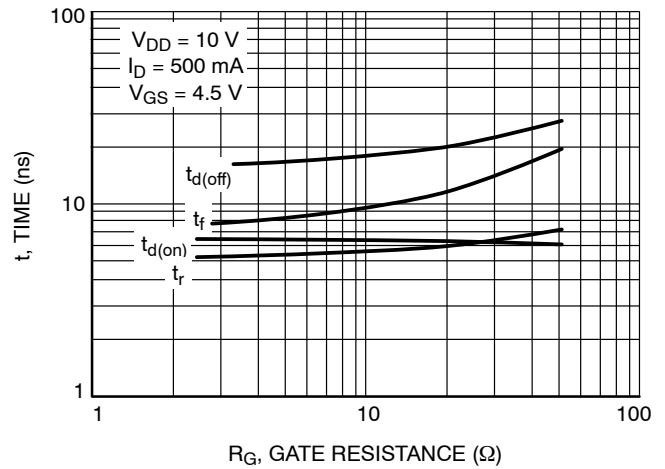


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

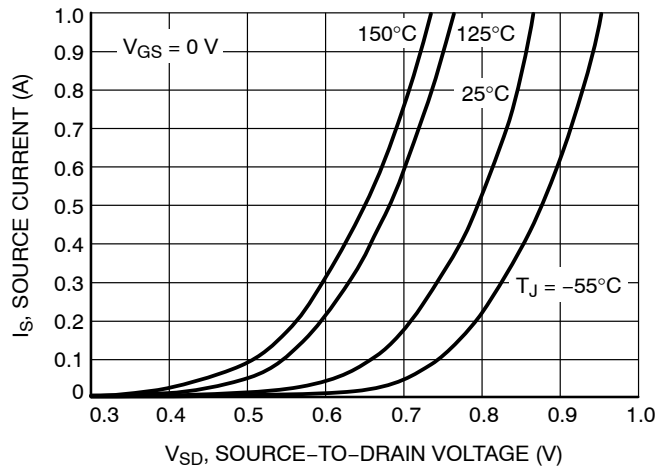
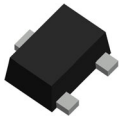


Figure 9. Diode Forward Voltage vs. Current

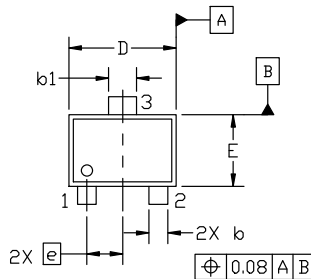


**SOT-723 1.20x0.80x0.50, 0.40P**  
**CASE 631AA**  
**ISSUE E**

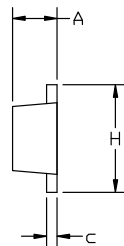
DATE 24 JAN 2024

NOTES:

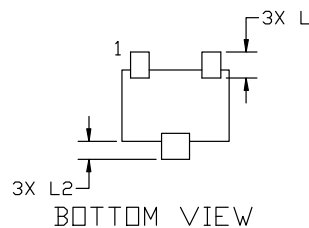
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



TOP VIEW

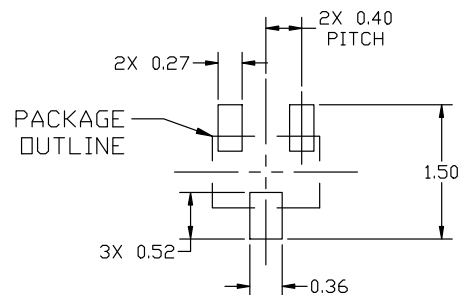


SIDE VIEW



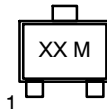
BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



RECOMMENDED MOUNTING  
FOOTPRINT

**GENERIC  
MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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